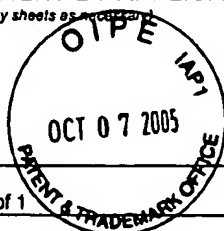


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|----------------------|-------------------|
| Application Number | 10/783,695 |
| Filing Date | February 20, 2004 |
| First Named Inventor | Forbes, Leonard |
| Group Art Unit | 2891 |
| Examiner Name | Smith, Bradley |

Sheet 1 of 1

Attorney Docket No: 1303.019US2

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| Application Number | Unknown |
| Filing Date | Even Date Herewith |
| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

Sheet 1 of 6

Attorney Docket No: 1303.019US2

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| Application Number | Unknown |
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| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

Sheet 2 of 6

Attorney Docket No: 1303.019US2

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| Application Number | Unknown |
| Filing Date | Even Date Herewith |
| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

Sheet 3 of 6

Attorney Docket No: 1303.019US2

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| | Application Number | Unknown |
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| | First Named Inventor | Forbes, Leonard |
| | Group Art Unit | Unknown |
| | Examiner Name | Unknown |
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| Application Number | Unknown |
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| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

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Sheet 5 of 6

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| Application Number | Unknown |
| Filing Date | Even Date Herewith |
| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

Sheet 6 of 6

Attorney Docket No: 1303.019US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

| Examiner Initials* | Cite No.† | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | † |
|-----------------------|--------------|---|---|
| JSKS | | YAN, J. , et al., "Structural and electrical characterization of TiO2 grown from titanium tetrakis-isopropoxide (TTIP) and TTIP/H2O ambients", <u>Journal Vac. Sci. Technol. B</u> , 14(3), (1996), pp. 1706-1711 | |
| JSKS | | ZHANG, H. , et al., "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", <u>Journal of The Electrochemical Society</u> , 148(4), (2001), F63-F66 | |

EXAMINER

DATE CONSIDERED 12/12/05

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. † Applicant's unique citation designation number (optional) ‡ Applicant is to place a check mark here if English language Translation is attached